



8 REF2

6 I/O3

7 I/O4

5 REF2

Low Capacitance TVS Diode Array

This diode array is configured to protect up to four data transmission lines acting as a line terminator, minimizing overshoot and undershoot conditions due to bus impedance as well as protect against over-voltage events as electrostatic discharges.

SPECIFICATION FEATURES

- DC Forward Current Max of 200mA
- Maximum Capacitance of 5.0pF at 0Vdc 1MHz Line-to-Ground
- Maximum Leakage Current of 0.5µA @ 100V
- Repetitive Peak Inverse Voltage of 200V
- Industry Standard SMT Package SOIC-8
- IEC61000-4-2, IEC61000-4-4 and IEC61000-4-5 Full Compliance
- 100% Tin Matte finish (LEAD-FREE PRODUCT)

APPLICATIONS

- Set Top Box Input/Output lines
- LAN/WLAN Access Point terminals
- Video Signal line protection
- I²C Bus Protection



SOIC-8

I/O1

REF1

REF1 3

I/O2 4

MAXIMUM RATINGS Tj = 25°C Unless otherwise noted

Rating	Symbol	Value	Units
Repetitive Peak Inverse Voltage	V _{RRM}	200	V
Continuous Reverse Voltage	V _R	100	V
Peak Pulse Current (8/20µs Waveform)	۱ _{PP}	24	А
Average Rectified Forward Current, Per Diode	l _{F(AV)}	200	mA
Power Dissipation, Tj = 85° C, I _F = 200mA, Per Diode	Ρ _D	300	mW
Operating Junction Temperature Range	Tj	-55 to +150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Soldering Temperature, t max = 10 s	ΤL	260	°C
Thermal Resistance, Junction to Ambient	R _{ÐJA}	200	°C/W





ELECTRICAL CHARACTERISTICS Tj = 25°C unless otherwise noted

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Repetitive Peak Inverse Voltage	V _{RRM}				200	V
Breakdown Voltage	V _{BR}	Ι _{BR} = 10μΑ	150			V
Forward Voltage (8/20µs Pulse)	V _F	l _{PP} = 1A			0.95	V
		l _{PP} = 10A			2.0	V
Reverse Leakage Current	I _R	$V_{R} = 100V$			0.5	μA
Off-State Junction Capacitance	CJ	0Vdc Bias, f =1 MHz Between I/O pins and REF2 (Ground)			5	pF
		0Vdc Bias, f =1 MHz Between I/O pins		2.2		pF





PACKAGE DIMENSIONS AND SUGGESTED PAD LAYOUT



